

IN THE SPECIFICATION

Please replace the paragraph beginning at page 6, line 11, with the following rewritten paragraph:

--The results found with this structure are surprisingly different from those found with high-energy retrograde wells: the results reported with high-energy retrograde wells did not show any major improvement over that for more conventional Ldmos.--

Please replace the paragraph beginning at page 1, line 1, with the following rewritten paragraph:

--This application claims priority from provisional 60/259,322 filed 12/31/00, which is hereby incorporated by reference.--

Please replace the paragraph beginning at page 16, line 13 with the following rewritten paragraph:

-- Figures 5A through 5C are a set of device cross-sections, showing how the device dimensions are scaled for different operating voltage specifications. However, note that the drift region length will scale with voltage (approximately one micron for each 25V), and this increase in length has not been shown. --

Please replace the paragraph beginning on page 16, line 8 with the following rewritten paragraph:

-- Metallization 419 (e.g. 500 to 800 nm of Al/Si/TiW stack) is then deposited, patterned and etched. As shown in Figure 4H, the metallization structure 419 connects the source 18 with the buried body 30. This produces the device structure of Figure 4H. Processing is then completed with conventional steps for further metallization if desired, encapsulation, contact pad exposure, etc. --